

## CDSV6-567-G

Forward Current: 0.15A  
Reverse Voltage: 75V  
RoHS Device

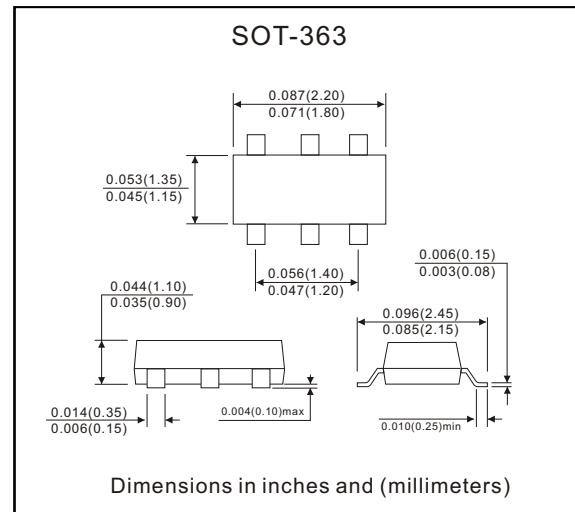
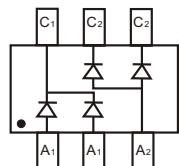


### Features

- Fast switching speed.
- Ultra small surface mount package.
- For general purpose switching applications.
- High conductance.

### Marking: KAC

### Diagram:



### Maximum Rating (at TA=25°C unless otherwise noted)

Parameter	Symbol	Limits	Unit
Peak repetitive peak reverse voltage Working peak reverse voltage DC blocking voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	75	V
Forward continuous current	I <sub>FM</sub>	300	mA
Averaged rectified output current	I <sub>O</sub>	150	mA
Non-repetitive peak forward surge current @t=1.0μS @t=1.0S	I <sub>FSM</sub>	2.0 1.0	A
Power dissipation	P <sub>D</sub>	200	mW
Thermal resistance, junction to ambient air	R <sub>θJA</sub>	625	°C/W
Operation junction temperature	T <sub>J</sub>	150	°C
Storage temperature range	T <sub>STG</sub>	-65 ~ +150	°C

### Electrical Characteristics (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Reverse breakdown voltage	I <sub>R</sub> =2.5μA	V <sub>(BR)R</sub>	75			V
Forward voltage	I <sub>F</sub> =1mA I <sub>F</sub> =10mA I <sub>F</sub> =50mA I <sub>F</sub> =150mA	V <sub>F1</sub> V <sub>F2</sub> V <sub>F3</sub> V <sub>F4</sub>			0.715 0.855 1.0 1.25	V
Reverse leakage current	V <sub>R</sub> =75V V <sub>R</sub> =20V	I <sub>R</sub>			2.5 0.025	μA
Junction capacitance	V <sub>R</sub> =0V, f=1.0MHz	C <sub>T</sub>			2	pF

# SMD Switching Diode Arrays

**COMCHIP**  
SMD Diodes Specialist

## ELECTRICAL CHARACTERISTIC CURVES (CDSV6-567-G)

Fig.1 Forward Characteristics

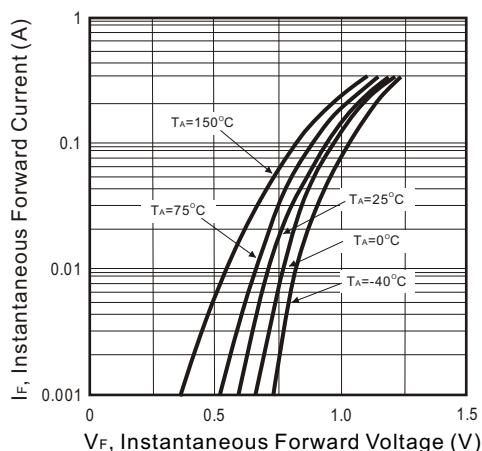


Fig.2 Reverse Characteristics

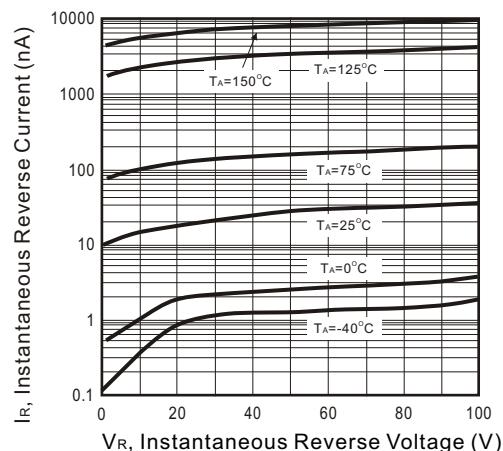


Fig.3 Capacitance Between Terminals Characteristics

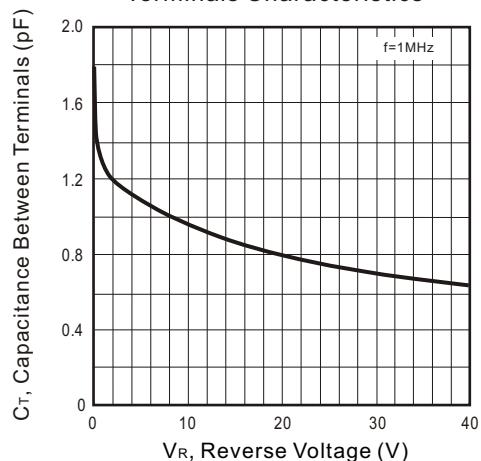


Fig.4 Power Derating Curve

